CERTIFICATE OF MAILING BY EXPRESS MAIL

I hereby certify that this paper or fee is being deposited with the United States Postal Service "Express Mail To Addressee" service under 37 C.F.R. §1.10 on the date indicated below and is addressed to: Commissioner for Patents, P.O. BOX 1450, Alexandria,

"Express Mail" Mailing Label Number

VA 22313-1450 926013142 US

(Date of deposit)

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicants: Xunming Deng

GAU: 1795; Conf. No.: 7826

Serial No.: 10/696,545

Examiner: Jeffrey Thomas Barton

Filed: October 29, 2003

Docket No.: 1-25574/PHYS00402

For: HYBRID WINDOW LAYER FOR PHOTOVOLTAIC CELLS

Mail Stop Amendments Commissioner for Patents, P.O. Box 1450 Alexandria, VA 22313-1450

AMENDMENT

Honorable Sir:

Responsive to the Office Action mailed November 14, 2007, please amend the above-identified application as indicated on the following pages.

If any fees are required pertaining to this response, Applicant(s) request that all necessary fees be charged to Deposit Account No. 13-0005.

Respectfully submitted,

Catherine B. Martineau

Reg. No. 31,854

MacMillan, Sobanski & Todd, LLC One Maritime Plaza, Fifth Floor 720 Water Street Toledo, Ohio 43604 (419) 255-5900

AMENDMENTS TO THE CLAIMS

Please amend the claims as follows:

1. (Currently Amended) A novel photovoltaic solar cell comprising: at least one absorber layer, and

at least one doped window layer having at least two sub-layers, wherein the first <u>sub-window layer</u> sub-window layer is adjacent the absorber layer and forms a desirable junction with the <u>absorber layer</u> absorber layer and wherein the second <u>sub-window layer</u> sub-window-layer is adjacent the first <u>sub-window layer</u> sub-window-layer and has high optical transmission;

wherein the absorber layer of the photovoltaic cell comprises a thin film silicon (tf-Si) alloy based solar cell including at least one of amorphous silicon (a-Si:H) based solar cell, amorphous silicon germanium (a-Si_(1-x)Ge_x:H) based solar cell, nanocrystalline silicon (nc-Si:H) based solar cell, microcrystalline silicon (μc-Si:H) based solar, polycrystalline silicon (poly-Si:H) based solar cell, or other combinations and mixtures thereof;

the first and second p-type sub-window layers having substantially the same chemical composition but having different bandgaps, wherein the second sub-window layer has a bandgap wider than the bandgap of the first sub-window layer, and wherein there is a minimal mismatch between the bandgap of the first sub-window layer and the bandgap of the absorber layer that is adjacent to the first sub-window layer.

2. - 10. Cancelled

- 11. (Original) The solar cell of claim 1, further comprising a substrate selected from at least one of: glass, metal or plastic.
- 12. (Currently Amended) The solar cell of claim 11, further comprising a suitable-transparent conductive oxide layer adjacent the second sub-window-layer.

13. Cancelled

14. (Original) The solar cell of claim 1, further comprising a buffer semiconductor layer between the absorber-layer and the first sub-window-layer.

15. - 74. Cancelled

- 75. (New) The solar cell of claim 1, the first sub-window layer being formed by deposition at a first temperature, and the second sub-window being formed by deposition at a second temperature that is lower than the first temperature.
- 76. (New) The solar cell of claim 1, the sub p-layer adjacent to the i-layer being formed after the i-layer is formed.
- 77. (New) The solar cell of claim 11, wherein the substrate comprises a stainless steel metal, the first and second sub-window layers comprise a-Si:H, the absorber layer comprises a-SiGe:H, and the n-layer comprises a-Si:H.
- 78. (New) The solar cell of claim 77, the first sub-window layer being formed by deposition at a first temperature, and the second sub-window being formed by deposition at a second temperature that is lower than the first temperature.